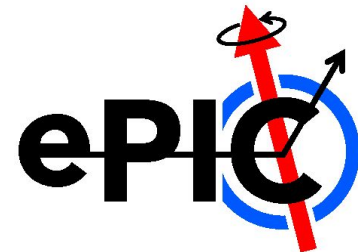




Istituto Nazionale di Fisica Nucleare

with DoE/eRD109 support

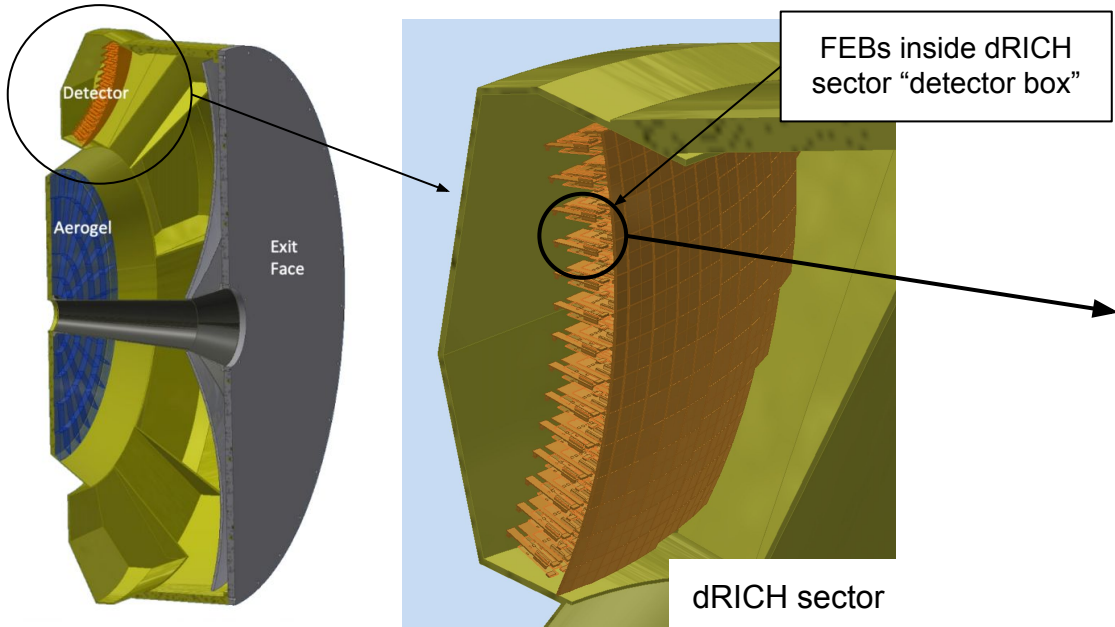


# The ALCOR ASIC for the dRICH Detector

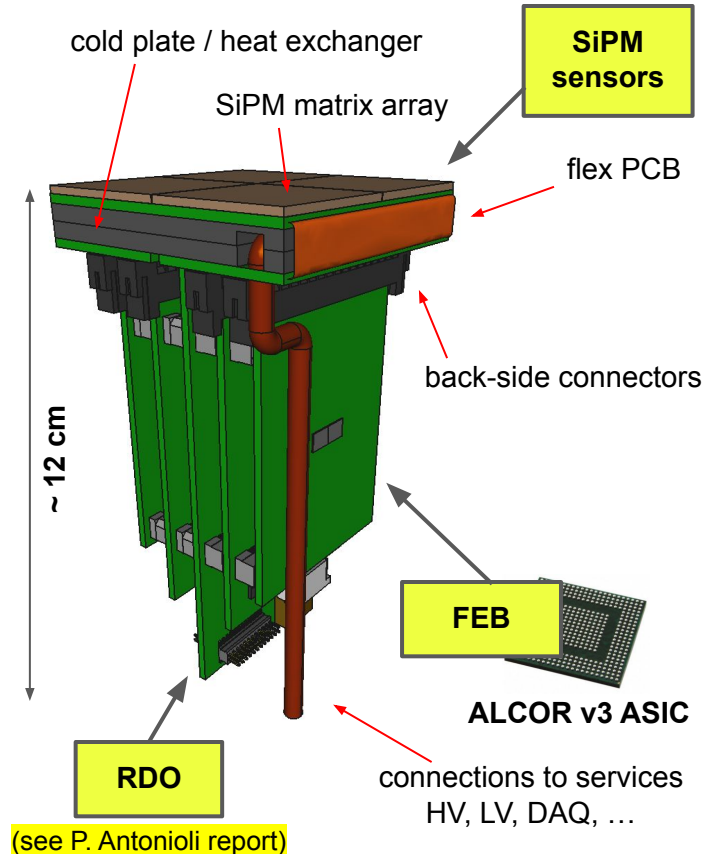
Fabio Cossio (INFN Torino)  
on behalf of the dRICH Collaboration

Incremental Preliminary Design and Safety Review of the  
EIC Detector DAQ and Electronics - 10<sup>th</sup> June 2024

# Requirements: space and number of channels



- 1 PDU: 4x64 SiPM array device (256 channels), 4 FEBs, 1 RDO
- 1 ALCOR (64 channels) per FEB: 8x8 SiPM matrix readout
- 1248 PDUs for full dRICH readout
- 4992 FEBs → 4992 ALCOR v3
- 319488 readout channels

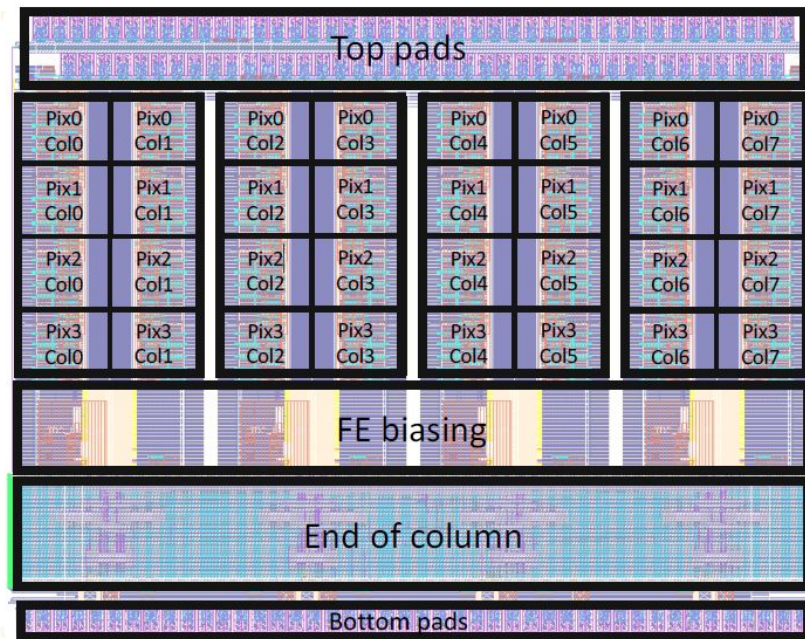


# Requirements: SiPM readout with single-photon sensitivity

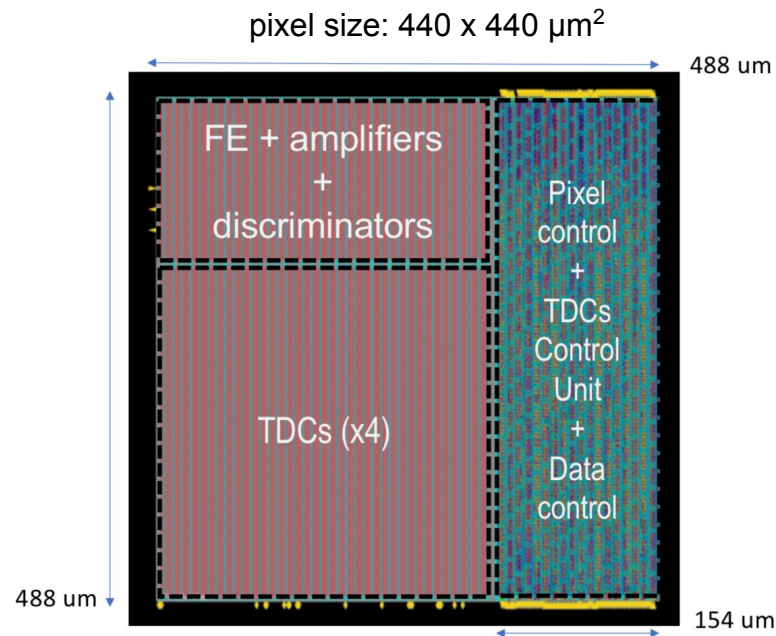
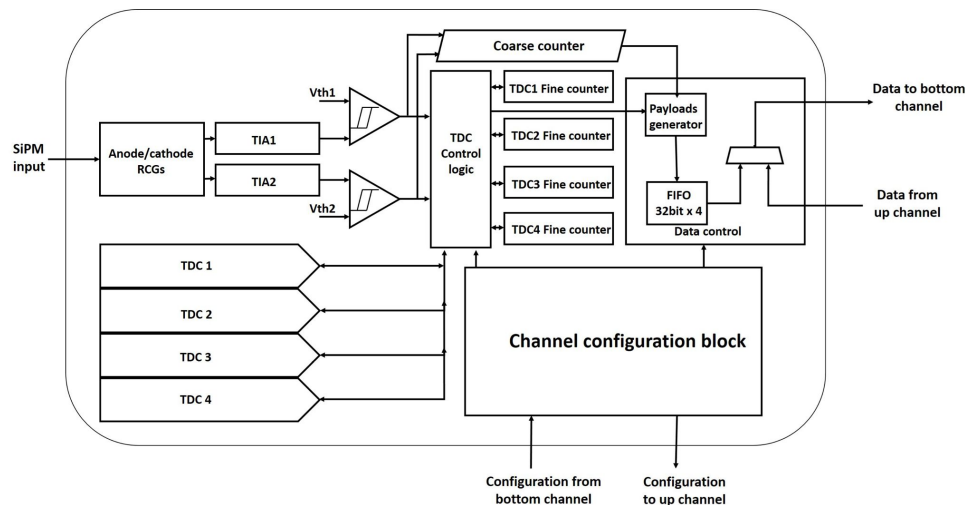
- ALCOR must provide **single-photon time tagging** of signals coming from SiPM sensors
- ALCOR must cope with **SiPM DCR: 300 kHz/channel** (at max SiPM radiation damage)

## ALCOR: A Low Power Chip for Optical Sensor Readout

- **32-pixel** matrix (8x4) mixed-signal ASIC (4.95 mm × 3.78 mm), new version will be **64-pixel** matrix (8x8)
- Single-photon time tagging + **Time-over-Threshold** or **Slew-Rate** measurements for **time walk correction**
- On-chip **signal amplification, conditioning** and **digitization**, 32-bit event word
- **Fully digital output**: 4 LVDS 320 MHz DDR Tx links
- Power consumption **~10-12 mW/channel**
- 0.11  $\mu\text{m}$  CMOS technology



# Implementation: pixel architecture



- **RCG input stage** current conveyor ( $Z_{in} = 10\text{-}20\ \Omega$ )
- **2 independent TIA branches** with 4 gain settings
- **2 leading edge discriminators** with independent (and per pixel) threshold settings (6-bit DAC)
- **4 TDCs** based on **analogue interpolation** with **25-50 ps time-bin** (at 320 MHz clock frequency)
- Pixel control logic handles TDC operation, pixel configuration and data transmission

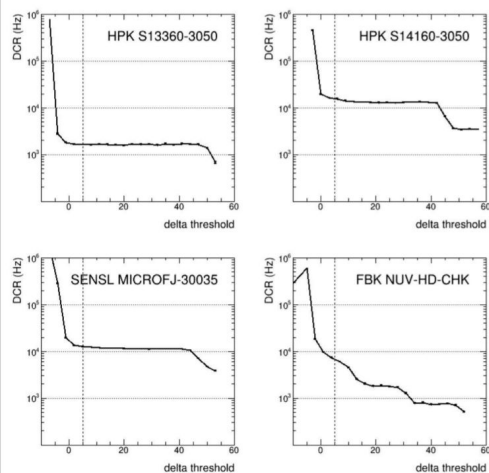
# Reminder: ALCOR v1

Developed by INFN for the readout of SiPMs at 77K, in the framework of Darkside (Dec 2019)

- Pixel matrix layout to explore solutions towards the development of an active silicon interposer for the integration of large area SiPMs for future massive frontier LAr Dark Matter Experiments

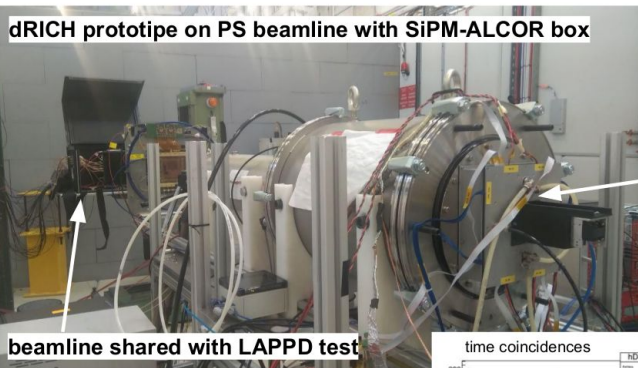


Extensively used within the EIC dRICH Collaboration during 2021-2022

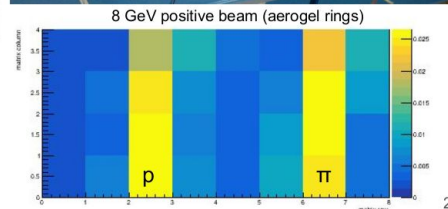
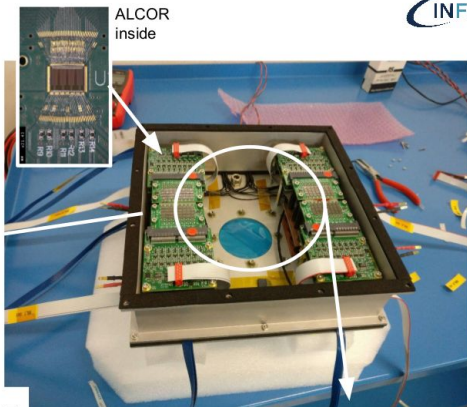
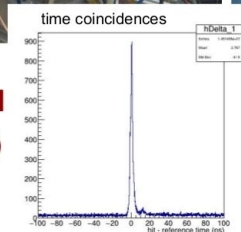


## 2022 test beam at CERN-PS

dRICH prototype on PS beamline with SiPM-ALCOR box



**successful operation of SiPM**  
**irradiated** (with protons up to  $10^{10}$ )  
**and annealed** (in oven at 150 C)



# Reminder: ALCOR v2



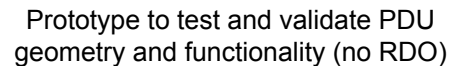
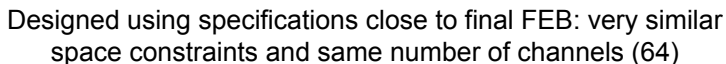
## ALCOR v2

- MPW, submitted in Dec 2022
- 60 chips, received in June 2023
- Includes new features targeted for EIC dRICH and bug fixes:
  - ✓ TDC logic critical error at high rates solved also for DCR rate at room temperature
  - ✓ New FE gain settings more suited for single photon applications
  - ✓ On-chip test-pulse also for EIC SiPM polarity
- Successfully validated in 2023 beam test

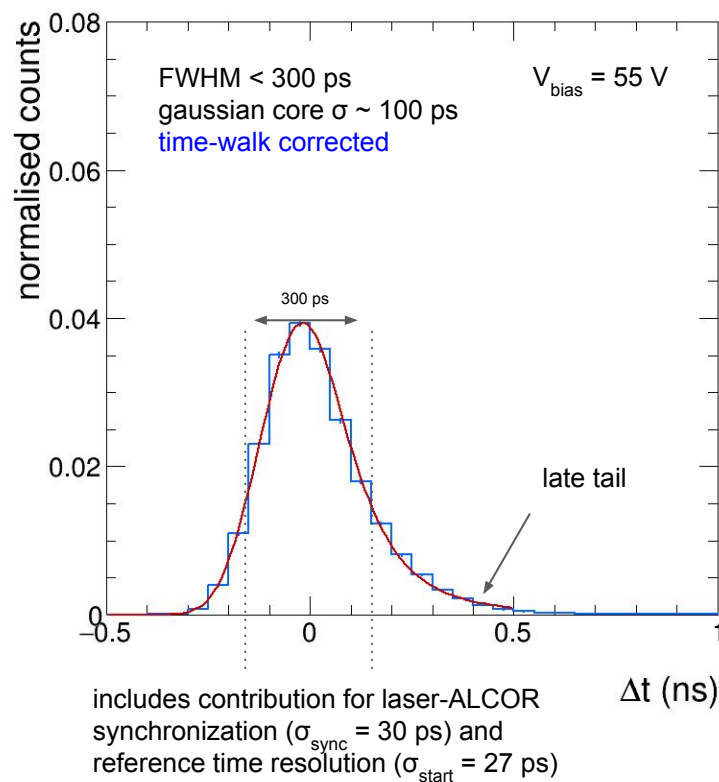
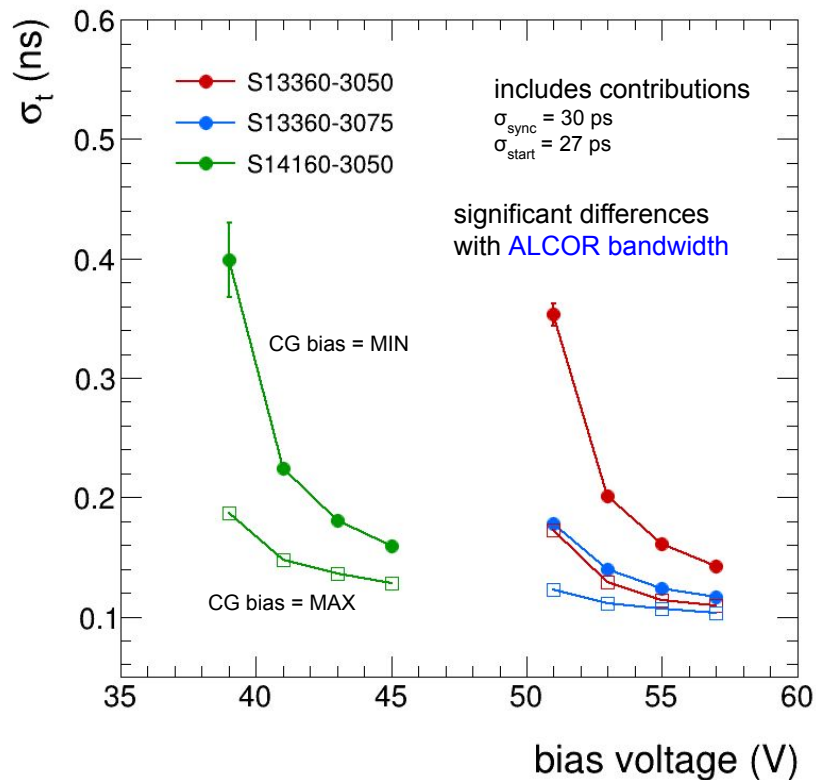
## ALCOR v2.1

- INFN internal engineering run, chips received in Jan 2024
- Includes small bug fixes w.r.t. ALCOR v2
- Very high number of chips available to increase instrumented area for dRICH prototype and assemble other test setups
- Version currently used: beam test (May-June 2024) to validate ALCOR-based dRICH readout and evaluate its performance

- Two **32-channel** ALCOR ASICs **wire-bonded** on the PCB
- **4 ALCOR-FE-DUAL** boards for each PDU (**256 channels**)
- System used for **2023-2024** ePIC dRICH beam tests



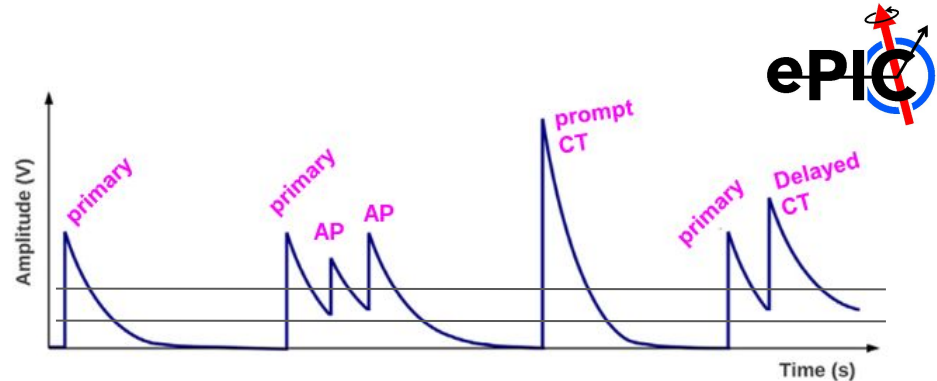
# Performance: laser timing measurements



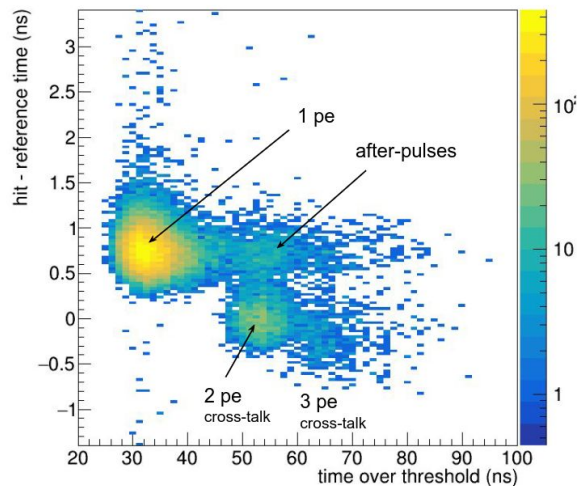
- Better time resolution with **75  $\mu\text{m}$  SPADs**
- Comfortably below  **$\sigma_t = 150$  ps** also at low  $V_{\text{bias}}$

# Time walk correction

**Time walk** correction needed to improve overall time resolution → studies with laser setup using **ToT** and **SlewRate** measurements



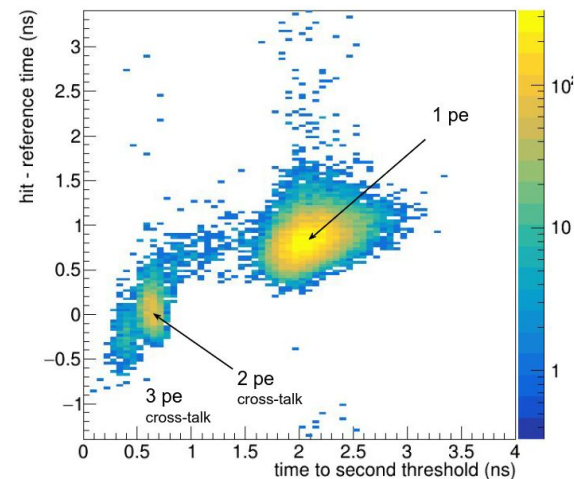
ALCOR ToT mode



✗ **ToT mode** cannot distinguish between afterpulses (slow-rise time, large ToT) and cross-talk (fast rise-time, large ToT)

✓ **SR mode** provides better separation

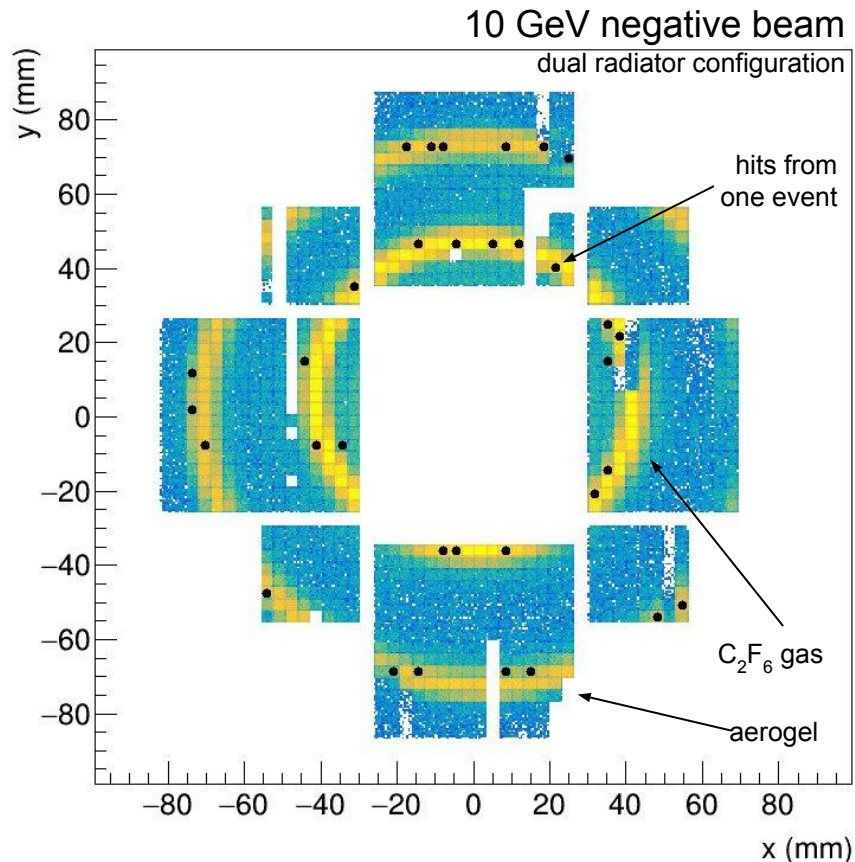
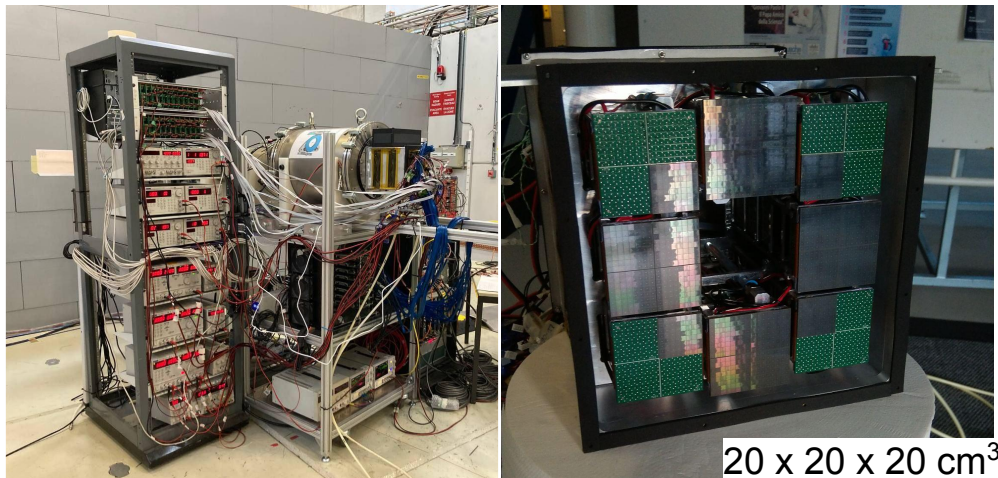
ALCOR slew-rate mode



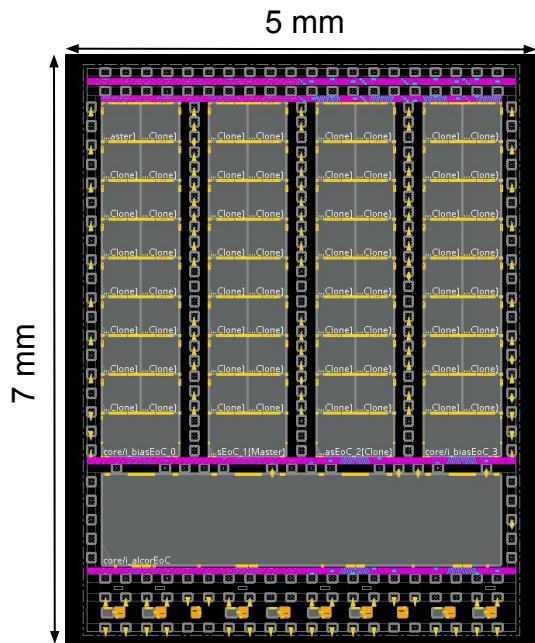
# Performance: 2023 test beam at CERN-PS

**Successful beam test with prototype dRICH and PDUs (CERN-PS, October 2023)**

- HPK S13360-3050 (3x3 mm<sup>2</sup>, **T = -30/-40°C**)
- 20 FE-DUAL (40 ALCOR v2.0, **1280 channels**)
- DAQ: Xilinx Kintex 7 KC705

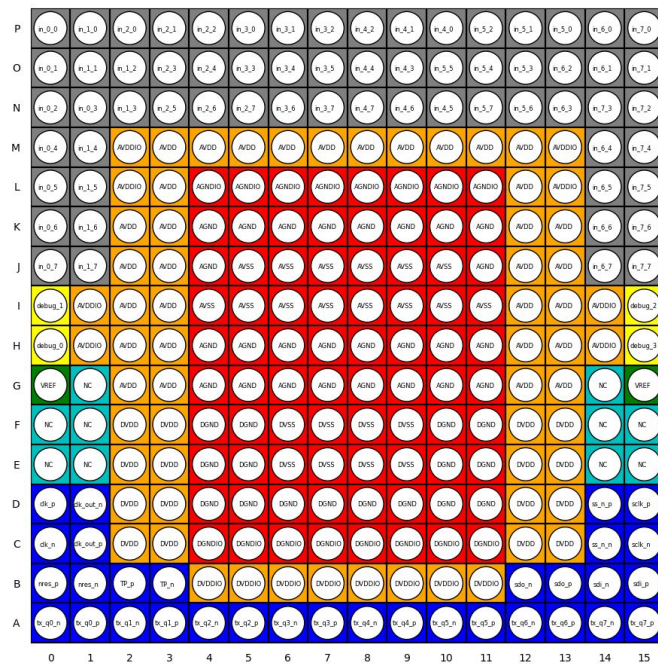
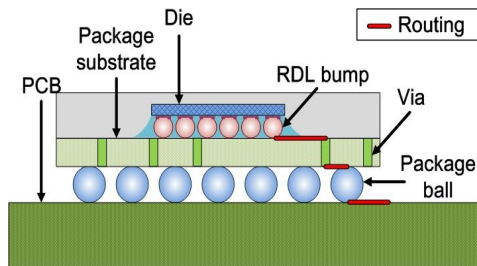


**ALCOR v3:** 64-channel ASIC, flip-chip BGA package



## 8x8 pixel matrix ASIC (64 channels)

- SiPM inputs bump pads between the pixel sectors
- Digital EoC in the bottom part



## 256 balls, 1mm pitch BGA package

- Power and ground on inner/mid contacts
- I/O on outer contacts

# ALCOR v3 requirements for EIC



## ePIC streaming data acquisition system (no traditional hardware trigger)

- **Digital shutter:** “inhibit” pixel digital logic to suppress out-of-gate DCR hits and **reduce data throughput**
- ~10.2 ns bunch crossing, ~300 ps bunch length, select **2-3 ns time window** → **3x-5x data reduction** before ALCOR digitization
- Asynchronous digital shutter implemented in ALCOR v3 pixel logic using external test-pulse signal
- **Programmable delay chain:** 4 configuration bits at channel-level (LSB  $\approx$  350 ps) and at the chip periphery (LSB  $\approx$  100 ps) to adjust offsets between different pixels and columns
- Shutter needed only when DCR becomes higher due to SiPMs taking radiation damage over time  
→ use first period of ePIC data taking to optimize **shutter calibration**

## Operation of ALCOR at multiple of **EIC clock frequency** (98.52 MHz)

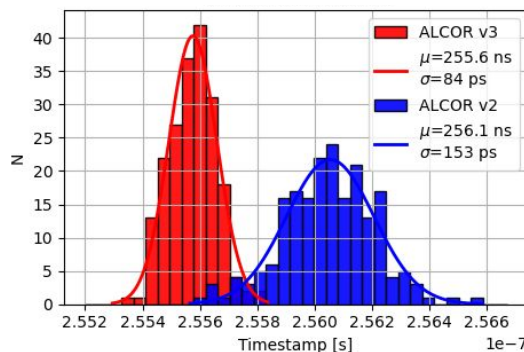
- Nominal ALCOR v3 clock frequency: 98.52 MHz x 4 = **394.08 MHz**
- Digital logic, TDCs and serializers/drivers re-implemented and verified at 394.08 MHz

# ALCOR v3 front-end

Small revisions on ALCOR FE design

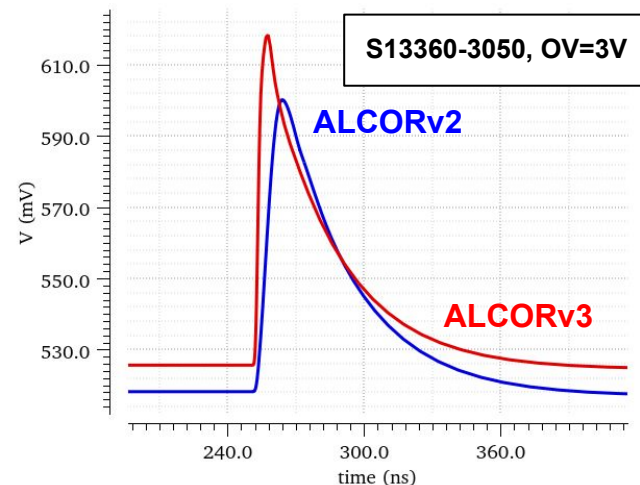
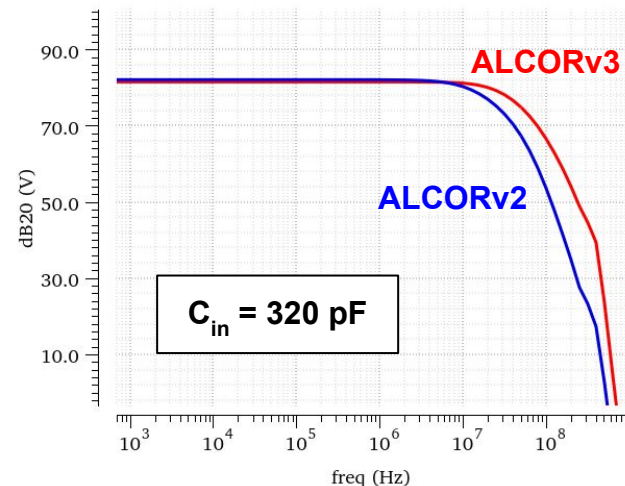
- **Increased amplifier bandwidth** to improve time resolution

- transient noise simulation
- $V_{th} = 0.5$  p.e.
- jitter: 153 ps  $\rightarrow$  84 ps



- **Hysteresis discriminator** to avoid re-triggering on slow tail with very low thresholds

➤ **Tape-out scheduled for Fall 2024**



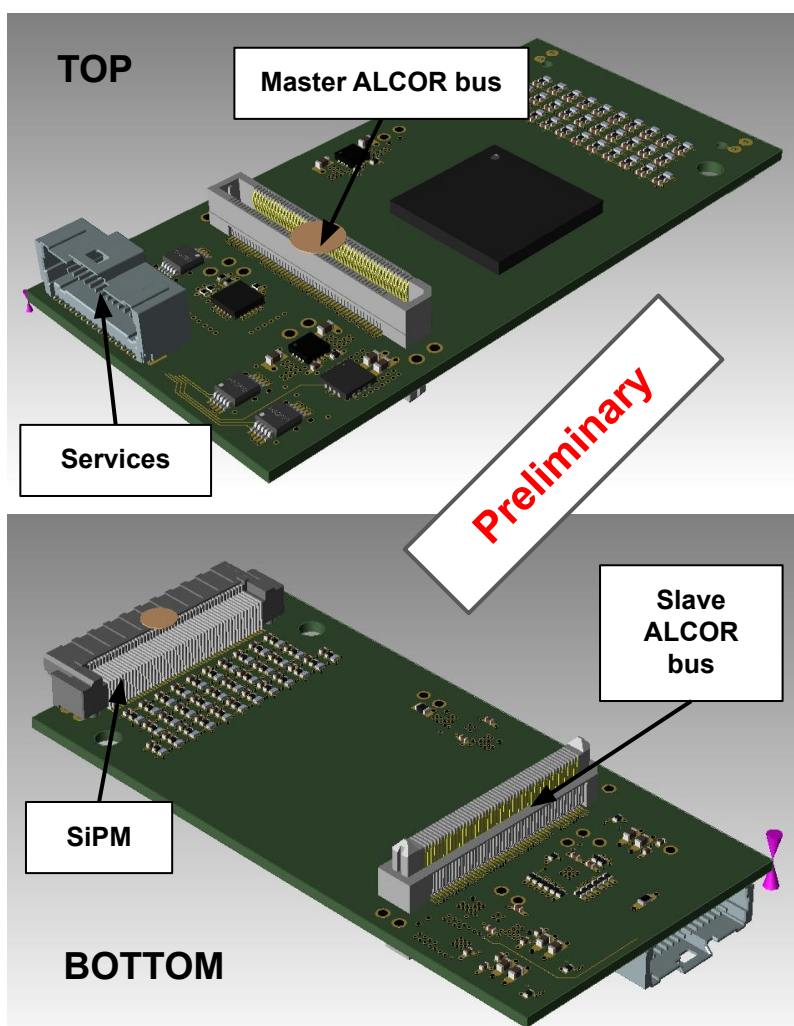
# ALCOR FEB

**Close cooperation with Bologna colleagues for RDO design, SiPMs requirements and space constraints**

Preliminary selection of connectors and components:

- **Master ALCOR bus** (between RDO and FEB, LVDS signals, see [P. Antonioli presentation](#)): *Samtec ERM5-050-04.0-L-DV-TR*
- **Slave ALCOR bus** (between first and second FEB, LVDS signals): *Samtec ERF5-050-05.0-L-DV-K-TR*
- **Services connector** (SiPM  $V_{\text{bias}}$  and  $V_{\text{annealing}}$ , ALCOR LV): *Molex 2035663007*
- **SiPM connector** (SiPM signals,  $V_{\text{bias}}$  and  $V_{\text{annealing}}$ ): *Samtec LSHM-150-01-L-RH-A-N-K-TR*

- Dedicated PCB section for SiPMs HV routing
- 2  $V_{\text{bias}}$  and 2  $V_{\text{annealing}}$  channels, up to 1 A each
  - **SiPM self-annealing**: forward-bias,  **$T=150^{\circ}\text{C}$**  on SiPM matrix board (see [ageing modeling and annealing procedures for SiPM DCR](#) in PreBrief)
  - FEB to support **T up to  $80\text{-}100^{\circ}\text{C}$**

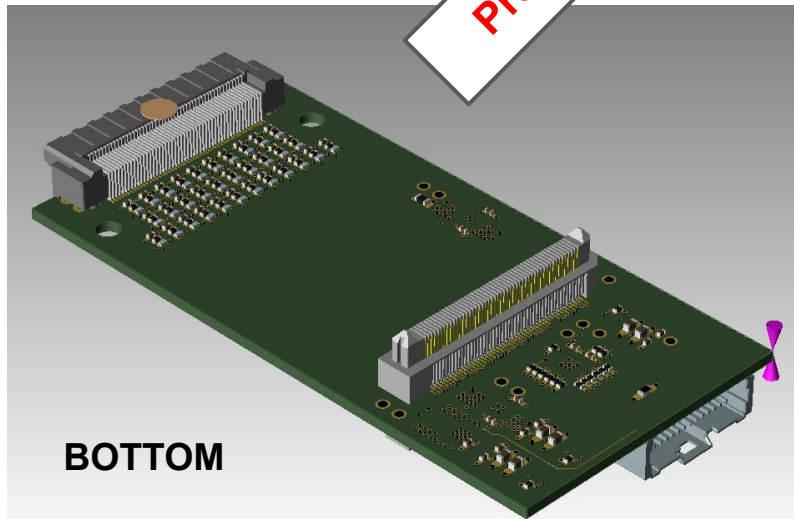
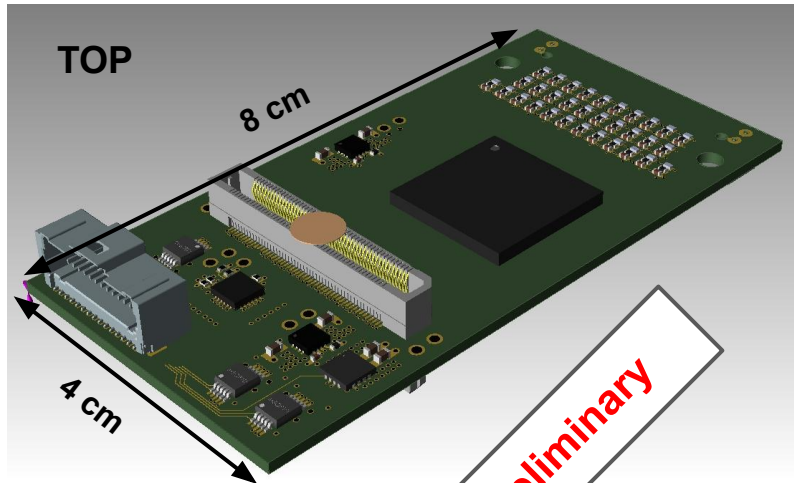


# ALCOR FEB

**Close cooperation with Bologna colleagues for RDO design, SiPMs requirements and space constraints**

Preliminary selection of connectors and components:

- **Linear Regulators** (2.5 V DVDD\_IO, 1.2 V DVDD, 1.2 V AVDD): *Analog Devices ADP1752ACPZ-2.5-R7, ADP1761ACPZ-R7*
- **Current monitors** (before regulators): *Microchip Technology MIC2040-1YMM-TR*
- **I2C to Parallel-Port Expander** (read/control regulators and current monitors → **single FEB power on/off granularity**): *Texas Instruments PCF8575RGER*
- **RC High Pass Filter** (AC-coupling between SiPMs and ALCOR)
- **Annealing circuit**: to be included



# Other requirements: radiation tolerance

The dRICH-PDUs are in a moderately hostile radiation environment

- $\Phi (p+n > 20 \text{ MeV}) = 200 \text{ Hz/cm}^2$
  - $\text{TID} \approx 650 \text{ rad (for } 1000 \text{ fb}^{-1}) < 1 \text{ krad}$
- } note these values include a safety factor 5

## SEU-SEL

- **Pixel** configuration registers and FSMs **already protected against SEU** in ALCOR v2
- TMR SEU **protection added also for periphery** configuration registers, Hamming code SEU protection for FSMs: Single Error Correction, Double Error Detection codes (SECDED)
- On board prevention of SEL: **current monitor** on FEB regulators

## TID

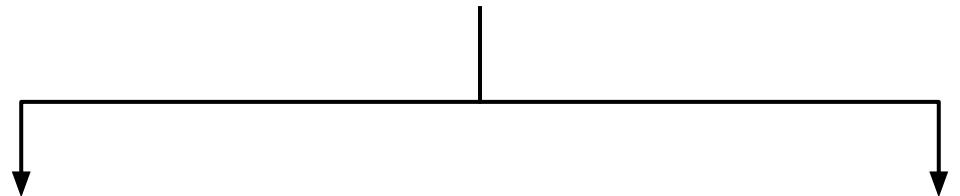
- Same technology already verified for TID up to a **few hundreds of krad**
- Also other FEB components will be tested and validated

- Irradiation tests campaign: SEU/SEL and TID tests at Centro of Proton-Therapy in Trento with ALCOR current version foreseen in July 2024

Our aim is to have the **first FEBs validated by Spring 2027** in order to begin the PDUs assembly

- Fall 2024: **ALCOR v3 MPW** tape-out and BGA package
- Spring 2025: ALCOR v3 BGA devices received → electrical characterization and integration tests

Evaluate readiness for mass production

- 
- A flowchart diagram with a central horizontal line. A vertical line descends from the center of this horizontal line, and two arrows point downwards from the ends of the horizontal line, branching the schedule into two parallel paths.
- Fall/Winter 2025: **ALCOR Engineering Run**
  - Summer 2026: start ALCOR mass production tests, FEBs assembly and validation
  - Fall 2025: **ALCOR v3.1 MPW** tape-out
  - Spring 2026: ALCOR v3 BGA devices received → electrical characterization
  - Summer 2026: **ALCOR Engineering Run**
  - Winter 2026: start tests of ALCOR mass production, FEBs assembly and validation

# ESH & QA plans



FEB produced following EU rules on restriction of hazardous substances (RoHS)  
ALCOR/FEB tests and validation managed by INFN Torino  
Safety rules enforced at INFN Torino Lab available [here](#)



The company charged to produce FEB:

- PCB electrical test
- RX analysis for BGA connections



## Test procedure:

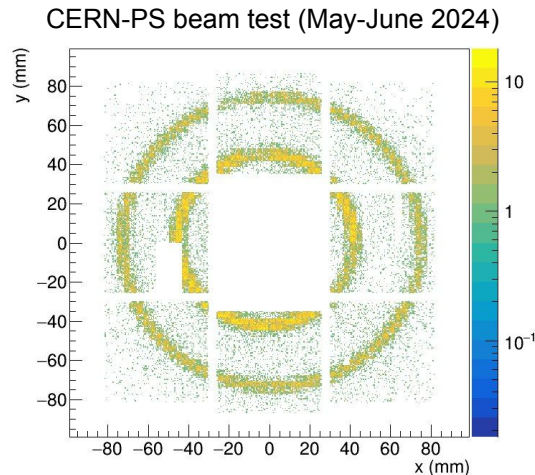
- Power-on, configuration, alignment, TDC scan, VTH scan, (SiPM DCR scan)
- Special test board card will be developed to test ALCOR/FEBs also without RDO
- Different options are currently being evaluated: in-house testing or external company
- FEB moved to PDU assembly line: test repeated with FEBs connected to PDU & RDO

**FEB (ALCOR) is part of INFN IKC:** compliance with US norms + delivery/acceptance procedures at BNL being specified in PPD

Reference documentation, test protocols and special cards for testbenches will be developed in 2026

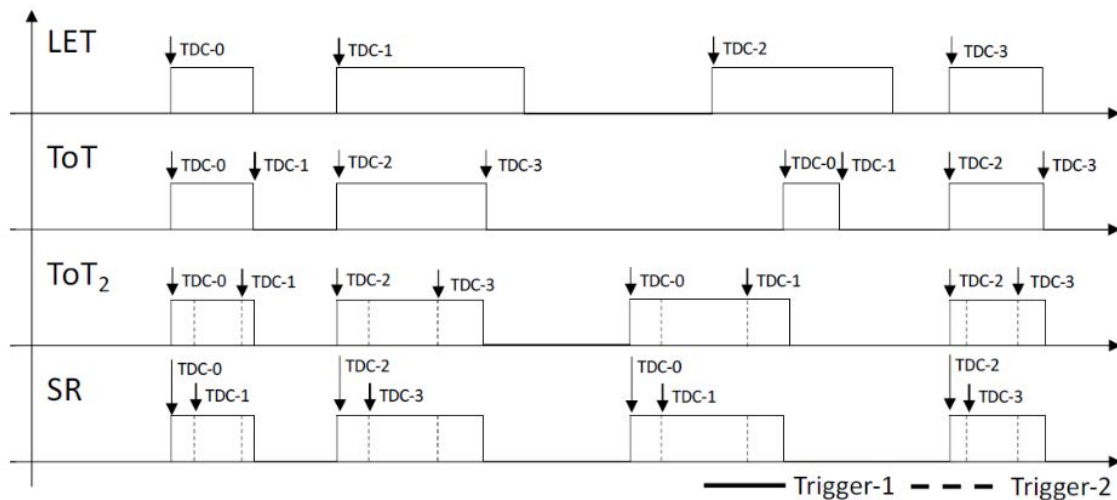
# Summary

- ALCOR fulfills dRICH requirements for SiPM readout
  - Several laboratory and beam tests demonstrated ALCOR-based readout **single photon sensitivity**, approaching 100 ps time resolution
  - New test beam at CERN-PS (May-June 2024) to validate the full system and evaluate its performance (2048 readout channels)
- Identified technical solutions to meet EIC-driven specifications
  - **Digital shutter** to reduce data throughput
  - New ALCOR **clock frequency**:  $98.52 \text{ MHz} \times 4 = \mathbf{394.08 \text{ MHz}}$
- Other design revisions for ALCOR new version defined
  - Analogue **FE optimization**, **hysteresis discriminator**
  - New chip layout for **BGA package**
  - **ALCOR v3 MPW tape-out in Fall 2024**
- FEB design ongoing to meet dRICH readout system requirements
  - **RDO** design: interface for data, configuration, control, services (more details in P. Antonioli talk)
  - **SiPMs** requirements: provide bias and annealing
  - **Space** constraints: 4 cm x 8 cm



# Backup Slides

# ALCOR pixel operating modes



4 operating modes:

- **LET:** leading edge measurement
- **ToT:** Time-over-Threshold measurement using the first discriminator for both edges
- **ToT<sub>2</sub>:** Time-over-Threshold measurement using both discriminators
- **SR:** slew-rate measurement

Each mode can be set to:

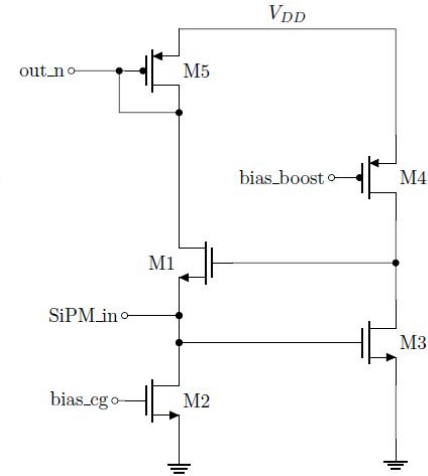
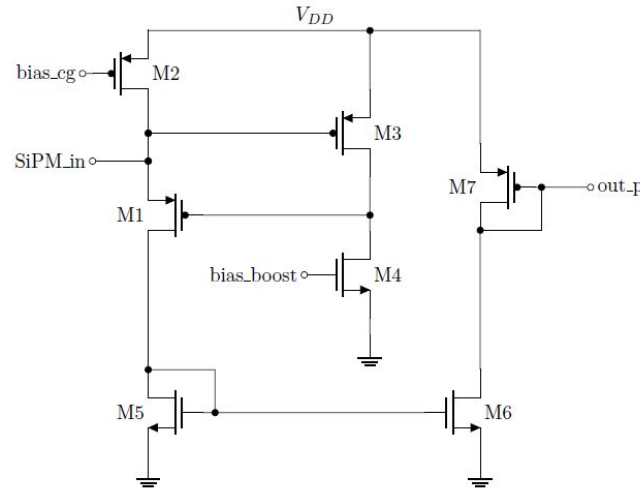
- **FE:** normal operation mode
- **FE\_TP:** send test-pulse to analogue front-end
- **TDC\_TP:** send test-pulse to pixel control logic to test and calibrate TDCs (bypass front-end)

Each pixel can also be disabled

# ALCOR Front-End

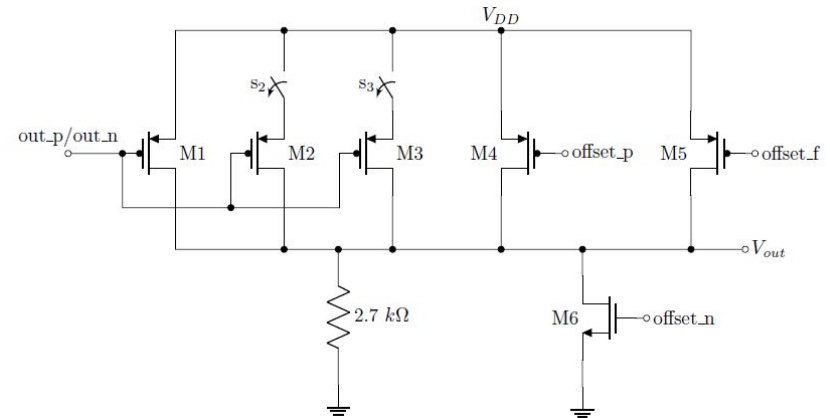
## Input stage

- Dual-polarity RCG current conveyor
- Programmable bias currents: CG (30-100  $\mu\text{A}$ ) and BOOST (1-4 mA)
- $Z_{in} \sim 10\text{-}20\ \Omega$



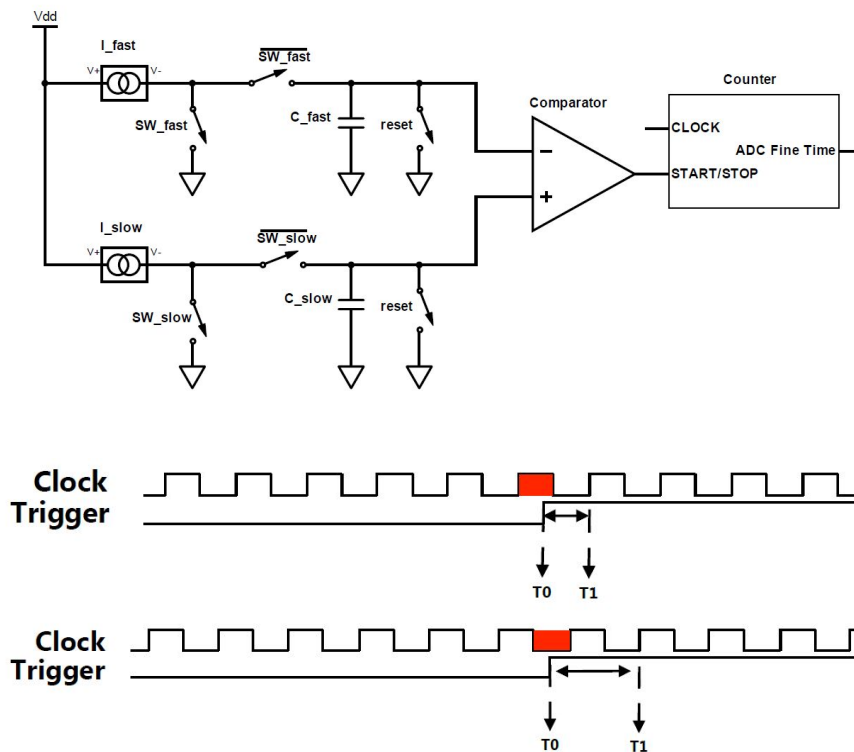
## Output stage

- TIA gain: 2.7 k $\Omega$
- 4 gain settings: 1/3, 4/3, 7/3 and 10/3
- DC coupled: baseline compensation based on gain and CG bias current settings + fine offset adjustment (3-bit)

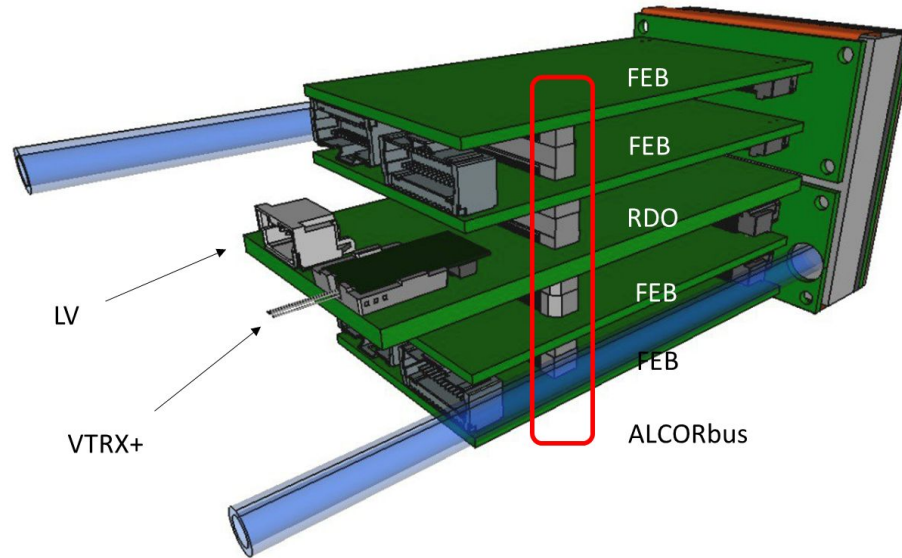


# Time to Digital Conversion

- Coarse time: 15-bit clock counter
- Time conversion performed by **TDC** based on **analogue interpolation** (9-bit fine time):
  - **fast ramp**: constant current to charge  $C_{fast}$  → measure phase between event trigger and clock
  - **slow ramp**: smaller constant current to charge  $C_{slow}$  → counts clock cycles until  $C_{slow}$  and  $C_{fast}$  are equal
- I.F. 64 or 128 → **LSB = 25-50 ps @320 MHz**
- Measured time interval: 0.5 - 1.5 clk period
- TDC conversion time: [200, 600] ns
- 4 TDCs per pixel for **event derandomization**



# ePIC dRICH photodetector unit (PDU)



# ALCOR QA → Mass production tests



Different options are currently being evaluated

- N. FEBs: 4992 → N. ALCOR: 4992 (to be increased to include QA, yield and lifetime)
- 7500 ALCOR → 85% yield → 6375 ALCOR
- Test time: 5-10 min./ALCOR (to be defined, test procedure used for ALCOR v2.1 as reference)
- 7500 ASIC · 10 min./ASIC = 75000 min. = 1250 h.

## Manual handling (in-house testing)

6 h./day · 5 days/week = 30 h./week

1250 h. / 30 h./week = 42 weeks ⇒ **10-11 months**

- **Parallel setups** to reduce time for mass testing (contribution from other INFN sections under discussion)
- After first batch, rest of production can be **tested in parallel with PDUs assembly** → no schedule delays

## Automated handler (external company)

24 h./day · 7 days/week = 168 h./week

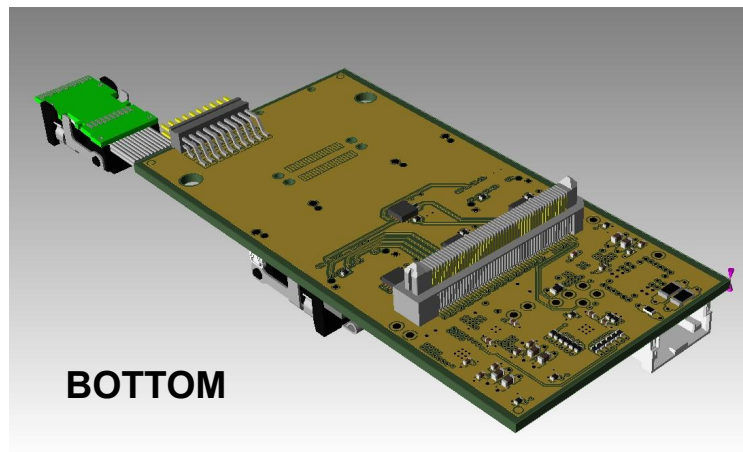
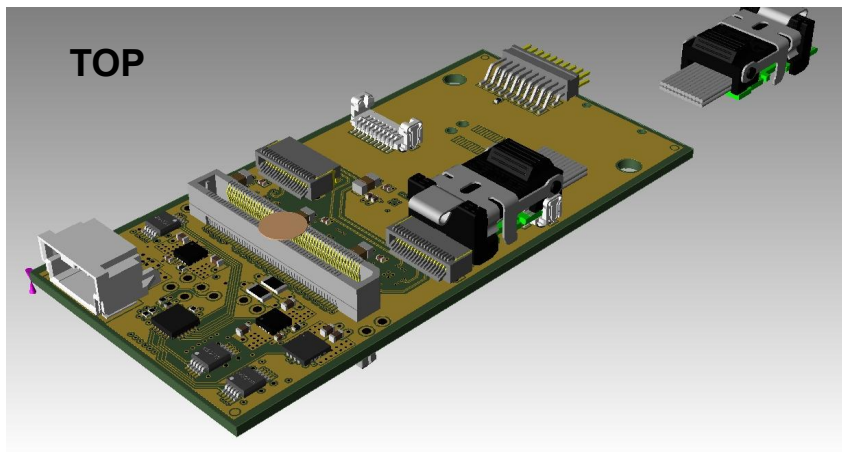
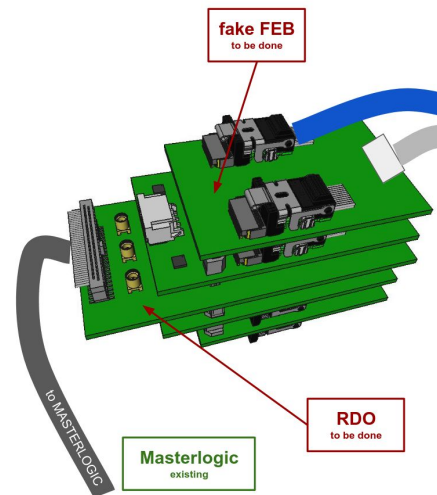
1250 h. / 168 h./week = 7-8 weeks ⇒ **2 months**

- Will require external company to perform the tests ( → **additional costs** )
- No manpower required for mass tests, but still requires manpower to develop and debug the test system

# “Fake” FEB

Support 2024-2025 dRICH activities when final FEB and ALCOR v3 are not available yet

- Allows integration tests of RDO with current ALCOR-FE-DUAL boards (already available and validated)
- 4 fake-FEBs + 1 RDO (still off-detector)



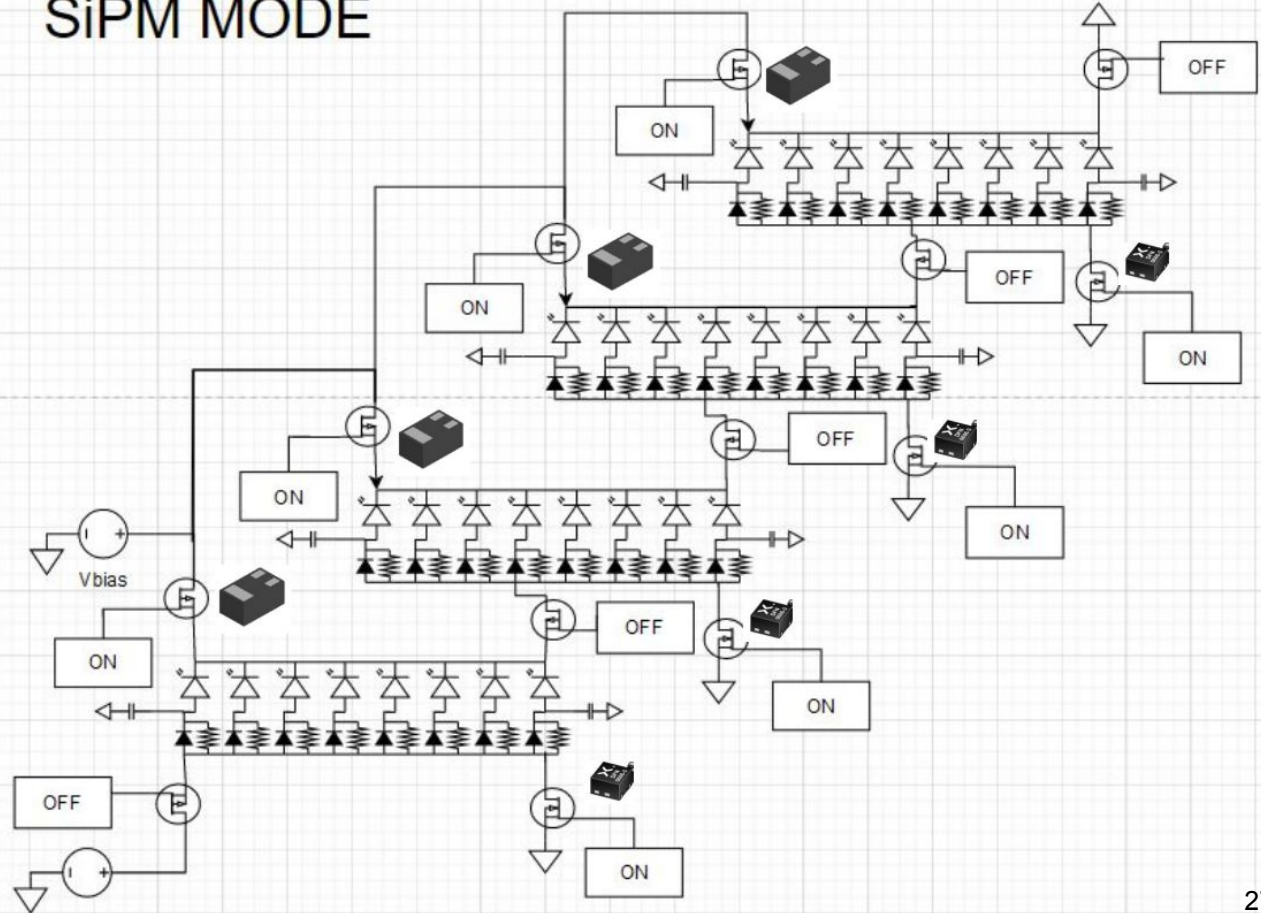
# Vbias distribution

the circuit foreseen to allow both normal operation of SiPM (reverse bias) and self-annealing (forward bias) allows to inhibit the Vbias to a granularity of 8 SiPM.

might come at handy in case of troubles with Vbias distribution in a specific SiPM  
→ inhibit Vbias in a string of 8 SiPM sensors while the rest of the PDU can still be operated

digital switches (MOSFET) controlled by RDO

## SiPM MODE



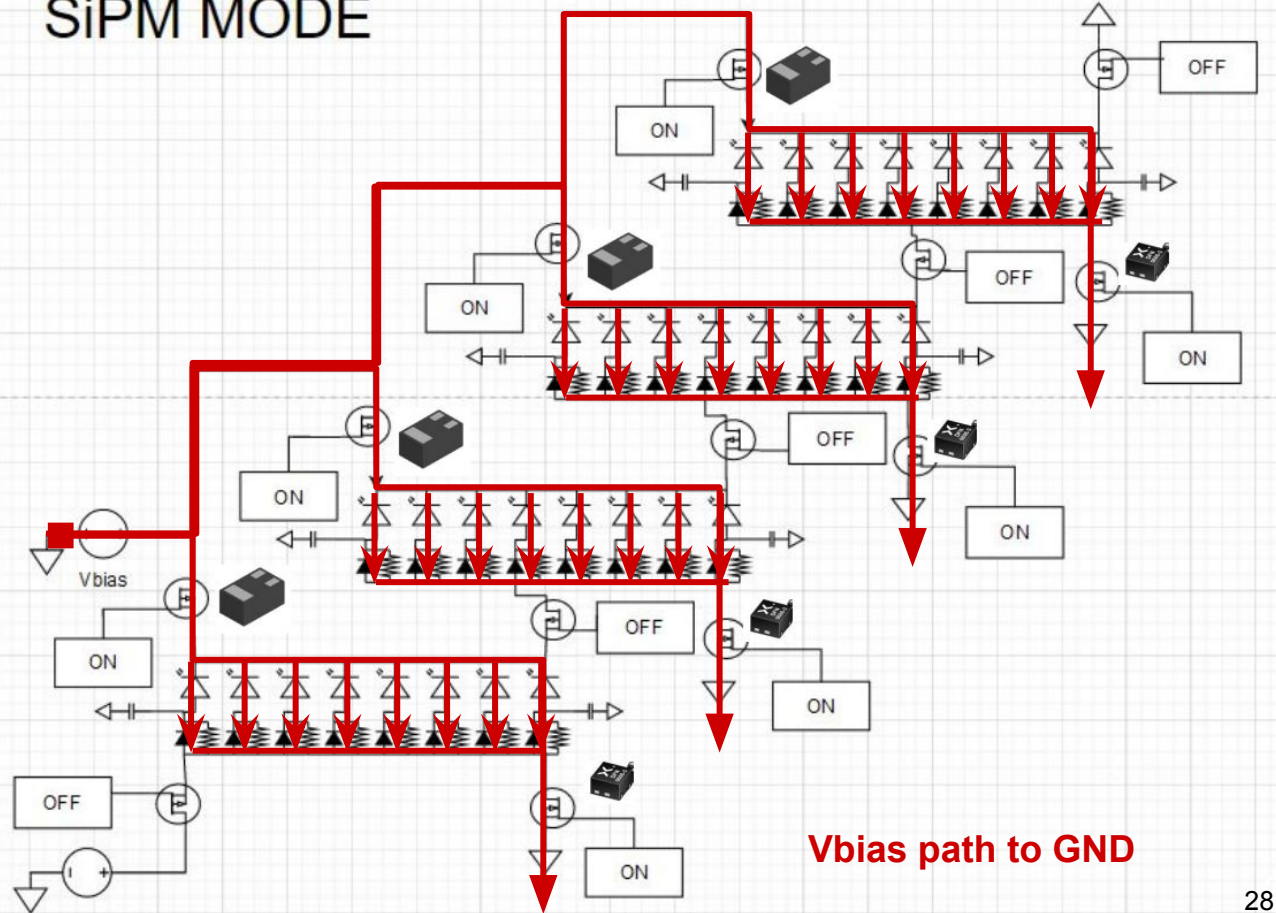
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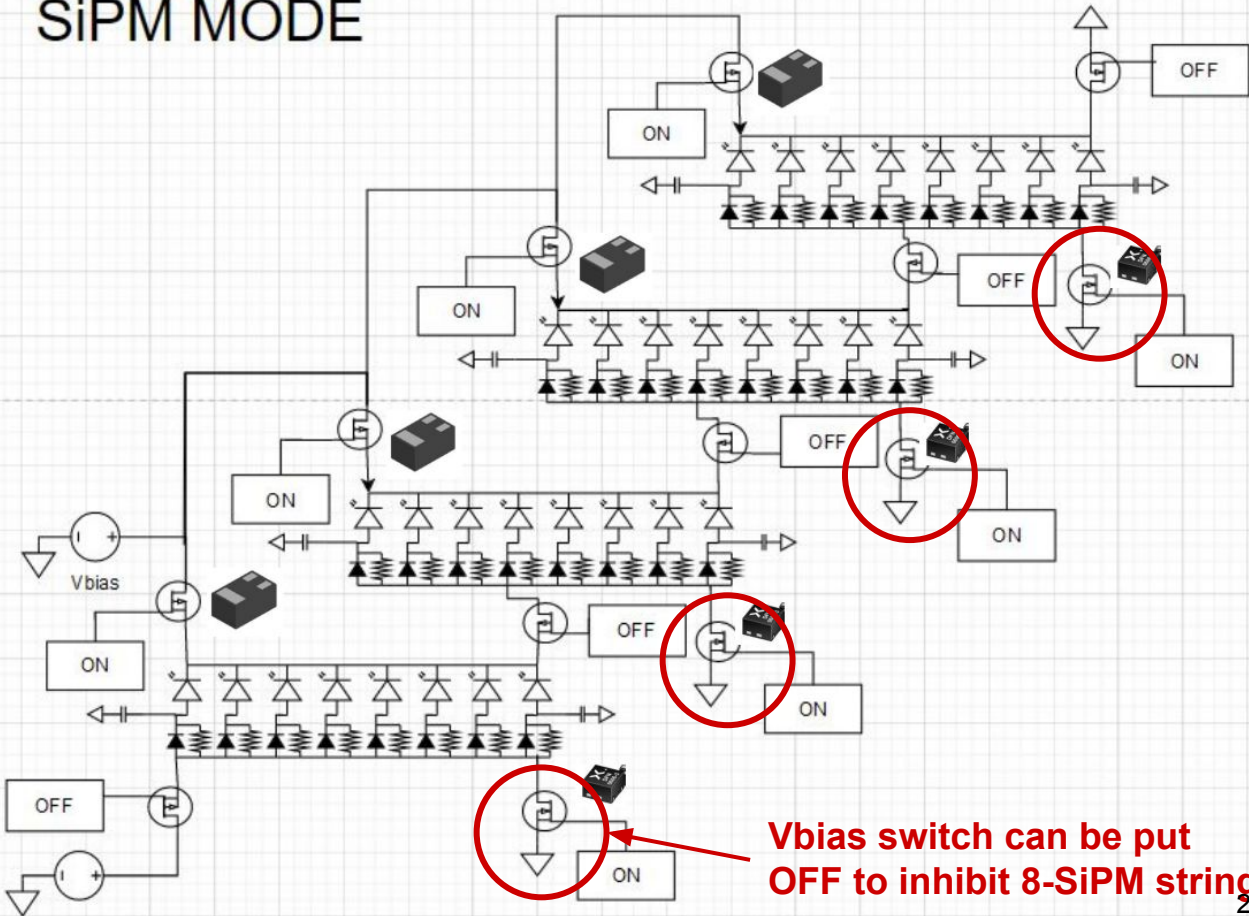
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digital switches (MOSFET) controlled by RDO

## SiPM MODE

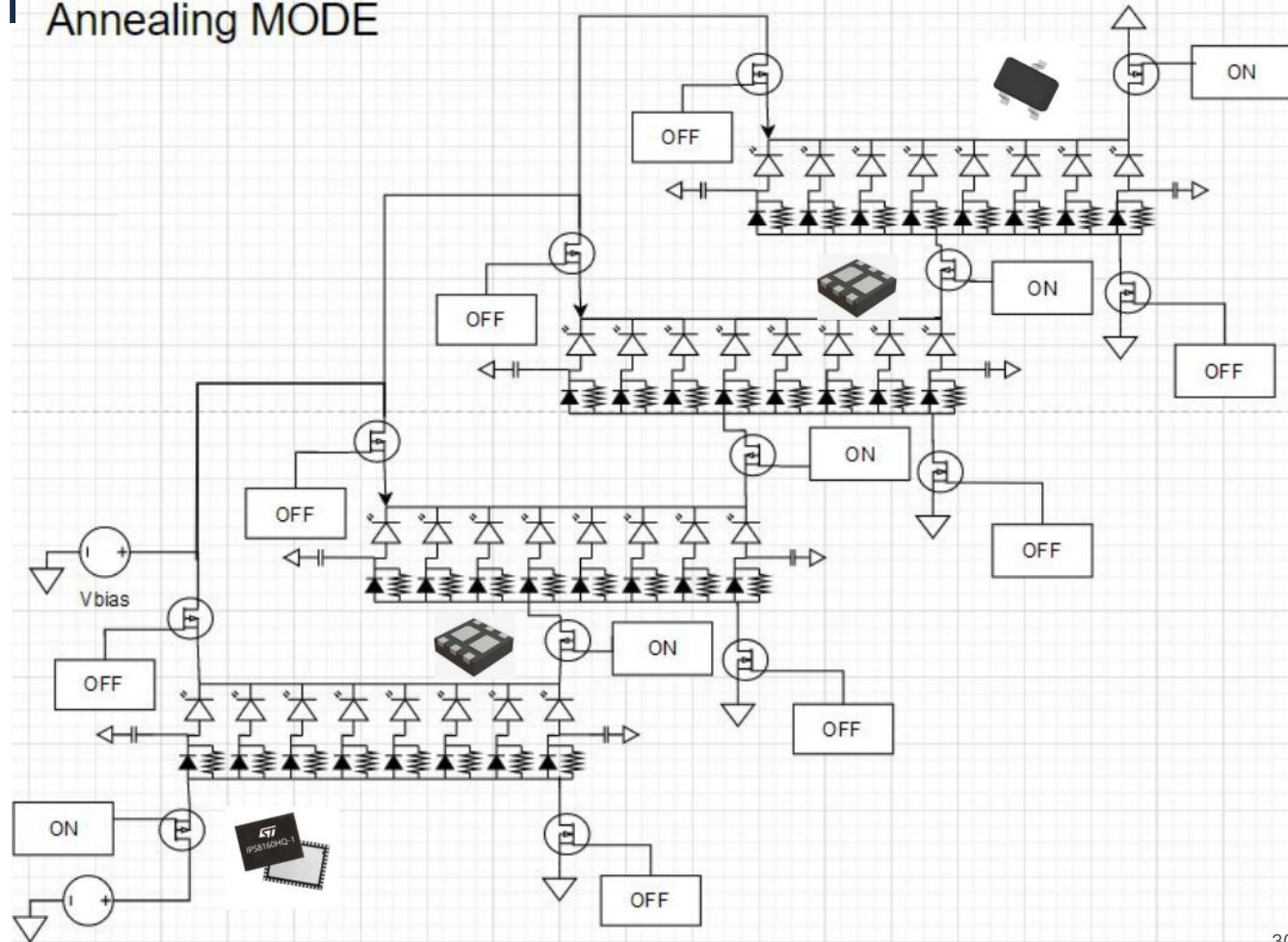


**Vbias switch can be put OFF to inhibit 8-SiPM string**

# Vann distribution

## Annealing MODE

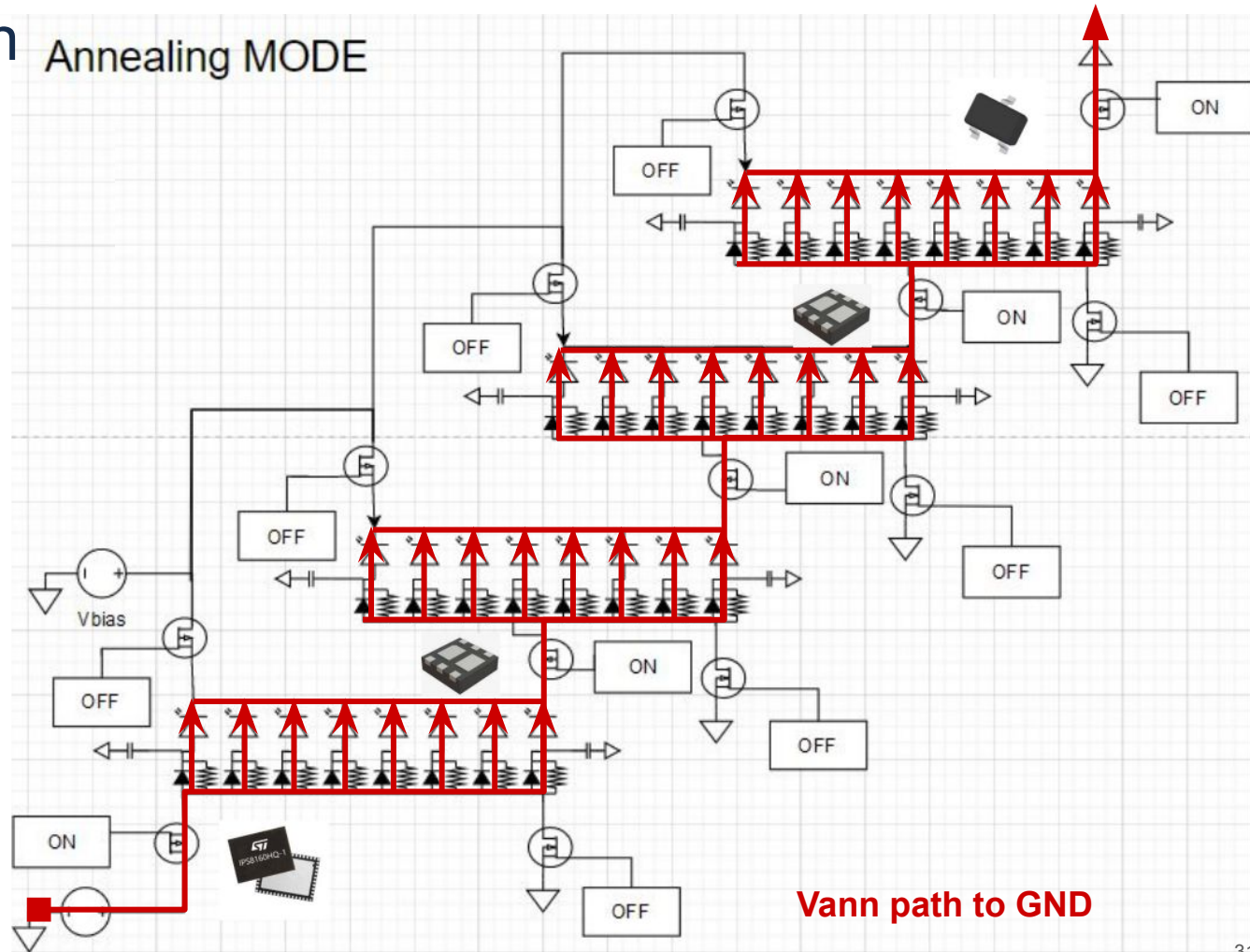
forward-bias annealing current for each sensor can reach up to 100 mA  
to keep annealing current low we foresee to forward-bias the SiPM in series of 4 SiPM strings



# Vann distribution

## Annealing MODE

forward-bias annealing current for each sensor can reach up to 100 mA  
to keep annealing current low we foresee to forward-bias the SiPM in series of 4 SiPM strings



**Vann path to GND**

# PDU voltage services

the **SiPM grouping** is composed of 4 strings of 8 SiPM each

one **SiPM matrix** is composed of two SiPM groupings

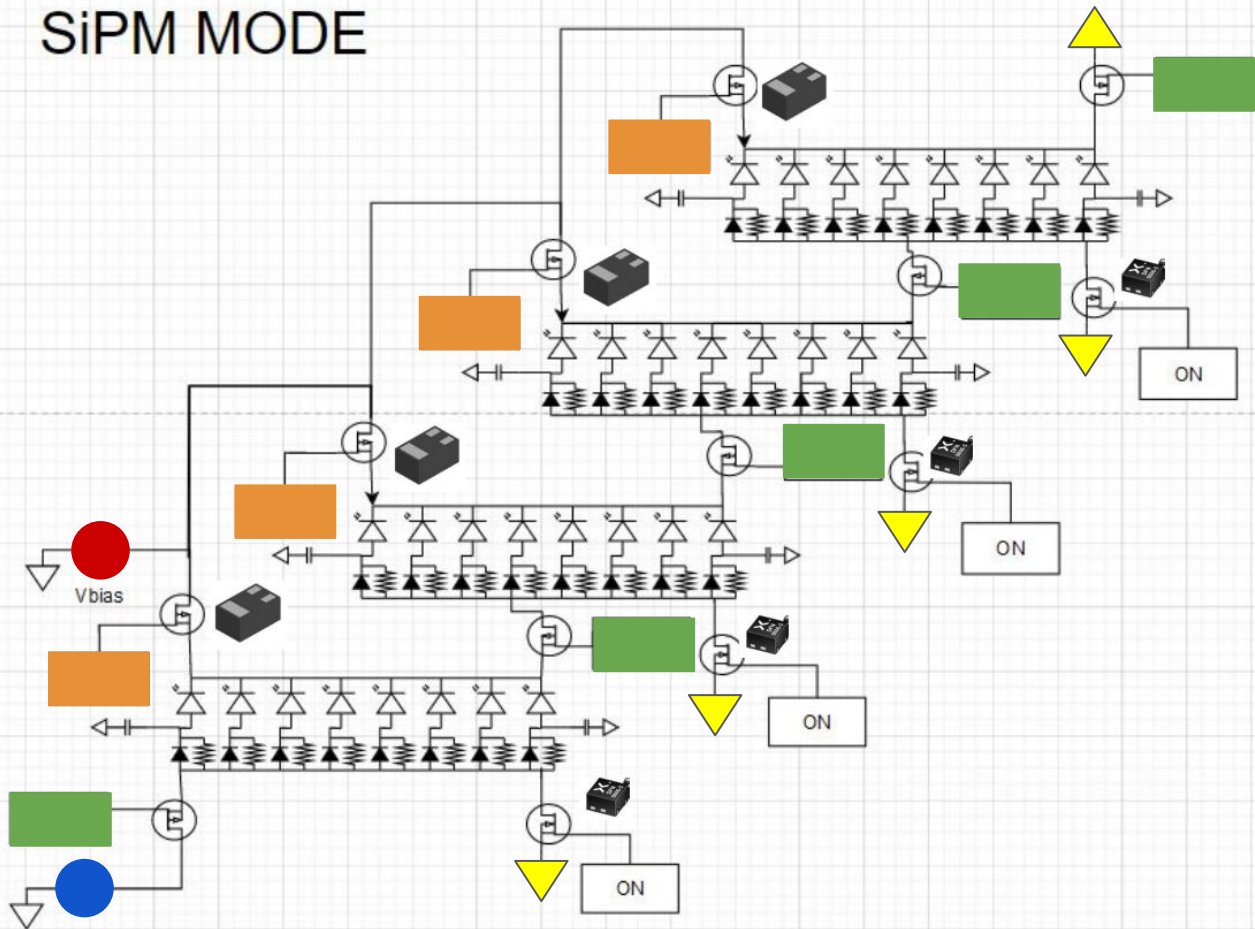
the **dRICH PDU** is composed of four SiPM matrices

for each SiPM grouping we foresee the following external services (via FEB)

- **1 V-bias**
- **1 CTRL-bias**
- **1 V-ann**
- **1 CTRL-ann**
- **1 GND**

This is a total of 5 wires for each SiPM grouping, namely a total of **40 wires for one PDU**. The 40 wires enter from the readout box patch-panel.

## SiPM MODE



# ALCOR for SiPM characterization measurements

